

★Under development

■ 5 V Single-Power-Supply Flash Memories

Capacity	Configuration (words×bits)	Erase block size (bytes)	Model No.	Access time (ns) MAX.	Supply voltage	Read current (mA) MAX. (f=10MHz)	Standby current (μA) MAX.	Operating temp. (°C)	Package
2M	256k × 8	16k	★LH28F020SUT/N-N60	60	V _{cc} = 5 V	60	100	0 to 70	32TSOP(I) Normal / 32SOP
			★LH28F020SUT/N-N80	80	V _{pp} = 5 V				
			★LH28F020SUHT/N-N80	80	V _{cc} = 5 V V _{pp} = 5 V				
4M	512k × 8	16k	LH28F004SUT-NF60	60	V _{cc} = 5 V	60	100	0 to 70	40TSOP(I) Normal
			LH28F004SUT-NF80	80	V _{pp} = 5 V				
			LH28F004SUHT-NF80	80	V _{cc} = 5 V V _{pp} = 5 V				
	512k × 8 256k × 16	16k	LH28F400SUE* <i>T/N</i> *-NF60	60	V _{cc} = 5 V	60	100	0 to 70	48TSOP(I) Normal / 56TSOP(I) Normal / 44SOP*
			LH28F400SUE* <i>T/N</i> *-NF80	80	V _{pp} = 5 V				
			LH28F400SUHE* <i>T/N</i> *-NF80	80	V _{cc} = 5 V V _{pp} = 5 V				
8M	1M × 8 512k × 16	64k	LH28F800SUT/R-70	70(120* ¹)	V _{cc} = 5 V (3.3 V read available)	60(35* ¹)	10	0 to 70	56TSOP(I) Normal / Reverse
			LH28F800SUT/R-10	100(150* ¹)	V _{pp} = 5 V				
			LH28F800SUHT/R-70	70(120* ¹)	V _{cc} = 5 V (3.3 V read available)				
			LH28F800SUHT/R-10	100(150* ¹)	V _{pp} = 5 V				
16M	2M × 8 1M × 16	64k	LH28F016SUT/R-70	70(120* ¹)	V _{cc} = 5 V (3.3 V read available)	60(35* ¹)	10	0 to 70	56TSOP(I) Normal / Reverse
			LH28F016SUT/R-10	100(150* ¹)	V _{pp} = 5 V				
			LH28F016SUHT/R-70	70(120* ¹)	V _{cc} = 5 V (3.3 V read available)				
			LH28F016SUHT/R-10	100(150* ¹)	V _{pp} = 5 V				
32M	4M × 8 2M × 16	64k	LH28F032SUTD-70	70(120* ¹)	V _{cc} = 5 V (3.3 V read available)	60(35* ¹)	20	0 to 70	56TSCP(I) Normal
			LH28F032SUTD-10	100(150* ¹)	V _{pp} = 5 V				

■ 3 V Single-Power-Supply Flash Memories

Capacity	Configuration (words×bits)	Erase block size (bytes)	Model No.	Access time (ns) MAX.	Supply voltage	Read current (mA) MAX. (f=10MHz)	Standby current (μA) MAX.	Operating temp. (°C)	Package
16M	2M × 8 1M × 16	64k	★LH28F016LLT/R-12	120	V _{cc} = 3 V	35	80	0 to 70	56TSOP(I) Normal / Reverse
			★LH28F016LLT/R-15	150	V _{pp} = 3 V				

■ Smart Voltage Flash Memories

Capacity	Configuration (words×bits)	Erase block size (bytes)	Model No.	Access time (ns) MAX.	Supply voltage	Read current (mA) MAX. (f=9MHz/5MHz [5 V/3 V])	Standby current (μA) MAX.	Operating temp. (°C)	Package
8M	1M × 8	64k	★LH28F008SCT/R/N/B-F85	85	Smart voltage* ²	35/14	100	0 to 70	40TSOP(I) Normal / Reverse /44SOP/42FBGA(CSP)
			★LH28F008SCT/R/N/B-F12	120					
			★LH28F008SCT/R/N/B-LF85	85	Smart voltage* ² (2.7 V read available)	35/14	100	0 to 70	40TSOP(I) Normal / Reverse /44SOP/42FBGA(CSP)
			★LH28F008SCT/R/N/B-LF12	120					
			★LH28F008SCT/R/N/B-F85	85	Smart voltage* ²	35/14	100	-25 to 85	40TSOP(I) Normal / Reverse /44SOP/42FBGA(CSP)
			★LH28F008SCT/R/N/B-F12	120					
			★LH28F008SCT/R/N/B-LF85	85	Smart voltage* ² (2.7 V read available)	35/14	100	-25 to 85	40TSOP(I) Normal / Reverse /44SOP/42FBGA(CSP)
			★LH28F008SCT/R/N/B-LF12	120					

*1 V_{cc} = at 3.3 V

*2 Smart voltage : Power supply is made an arbitrary selection among 3.3 V single-, 3.3 V/5 V-, 3.3 V/12 V-, 5 V single- and 5V/12 V- power supply without using control signals.